

preliminary

CMY25115NL-252

## 150V N-Channel MOSFET

### Features

- 100% EAS Guaranteed
- Green Device Available
- Super Low Gate Charge
- Excellent CdV/dt effect decline
- Advanced high cell density Trench technology

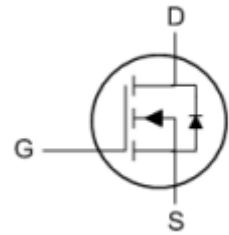
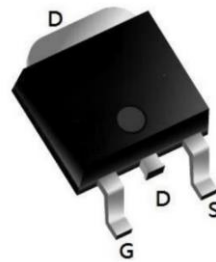
### Applications

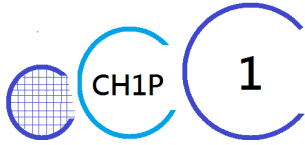
- Synchronous Rectification in SMPS
- Hard Switching and High Speed Circuit
- Power Tools
- UPS
- Motor Control

### Product Summary

Item	Typical Value	Unit
$V_{DS}$	150	V
$R_{DS(on)} @ V_{GS} = 10V (Max)$	88	m $\Omega$
$I_D$	20	A

### TO252 Pin Description





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**Absolute Ratings** ( $T_A = 25^\circ\text{C}$  unless otherwise noted)

Parameter	Symbol	Value	Units
Drain-Source Voltage	$V_{DS}$	150	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	V
Continuous Drain Current, $T_C = 25^\circ\text{C}$	$I_D$	20	A
Single Pulse Avalanche Energy (L=0.1mH)	EAS	53	mJ
Total Power Dissipation	$P_D$	53	W
Junction Temperature Maximum	$T_{JMAX}$	175	$^\circ\text{C}$
Storage Temperature	$T_{Storage}$	-55 to 175	$^\circ\text{C}$

**Thermal Characteristics**

Parameter	Symbol	Value	Units
Thermal Resistance Junction-Ambient	$R_{\theta JA}$	60	$^\circ\text{C}/\text{W}$

### Electrical Characteristics

Static ( $T_J=25^{\circ}\text{C}$ unless otherwise specified)						
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Units
Drain-Source Breakdown Voltage	$BV_{DSS}$	$V_{GS} = 0V, I_D = 250\mu A$	150	---	---	V
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = 120V, V_{GS} = 0V$	---	---	1	$\mu A$
Gate-Body Leakage Current	$I_{GSS}$	$V_{GS} = \pm 20V, V_{DS} = 0V$	---	---	$\pm 100$	nA
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS} = 10V, I_D = 10A$	---	---	88	m $\Omega$
		$V_{GS} = 4.5V, I_D = 10A$	---	---	100	
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\mu A$	1.2	---	2.5	V
Diode Forward Voltage	$V_{SD}$	$I_S = 1A, V_{GS} = 0V$	---	---	1.2	V
Dynamic ( $T_J=25^{\circ}\text{C}$ unless otherwise specified)						
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Units
Input Capacitance	$C_{iss}$	$V_{GS} = 0V, V_{DS} = 25V, f = 1MHz$	---	2285	---	pF
Output Capacitance	$C_{oss}$		---	110	---	
Reverse Transfer Capacitance	$C_{rss}$		---	83	---	
Total Gate Charge	$Q_g$	$V_{DS} = 75V, I_D = 10A, V_{GS} = 4.5V$	---	25.1	---	nC
Gate-Source Charge	$Q_{gs}$		---	6.8	---	
Gate-Drain Charge	$Q_{gd}$		---	12.6	---	
Turn-on delay time	$T_{d(on)}$	$V_{DS} = 75V, I_D = 10A, V_{GS} = 10V, R_G = 3.3\Omega$	---	13	---	nS
Rise time	$T_r$		---	8.2	---	
Turn-off delay time	$T_{d(off)}$		---	25	---	
Fall time	$T_f$		---	11	---	

Typical Characteristics

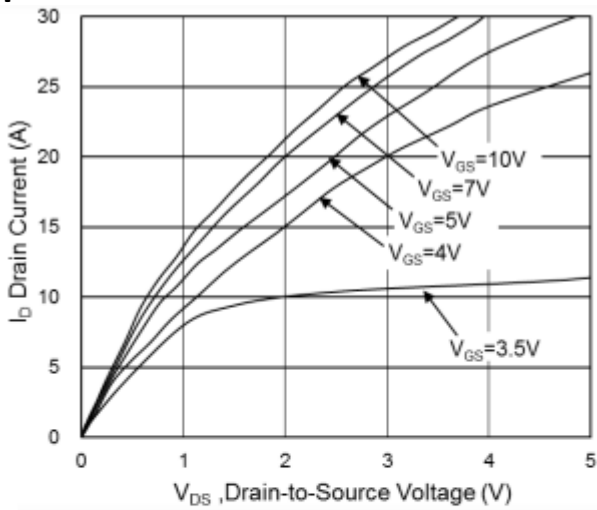


Fig.1 Typical Output Characteristics

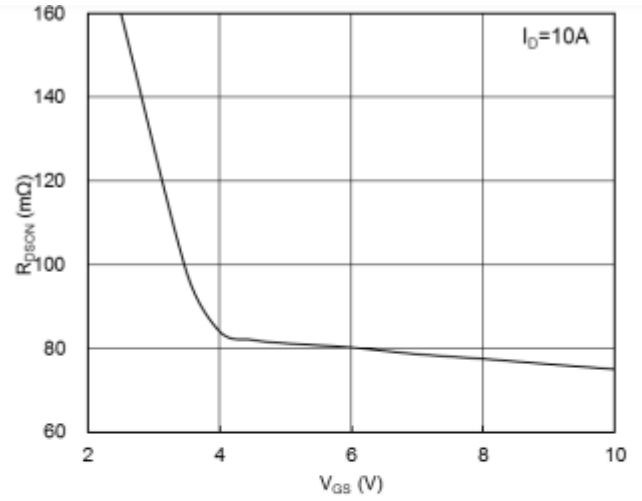


Fig.2 On-Resistance vs. Gate-Source Voltage

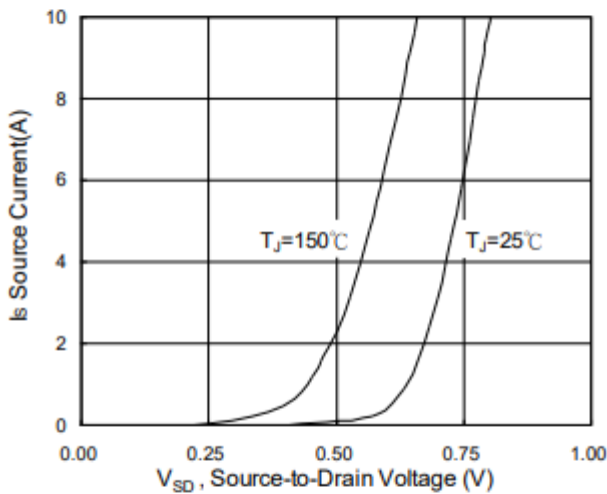


Fig.3 Forward Characteristics of Reverse

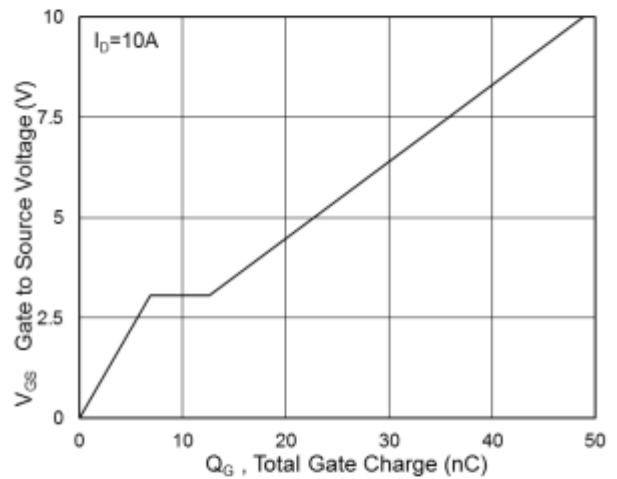


Fig.4 Gate-Charge Characteristics

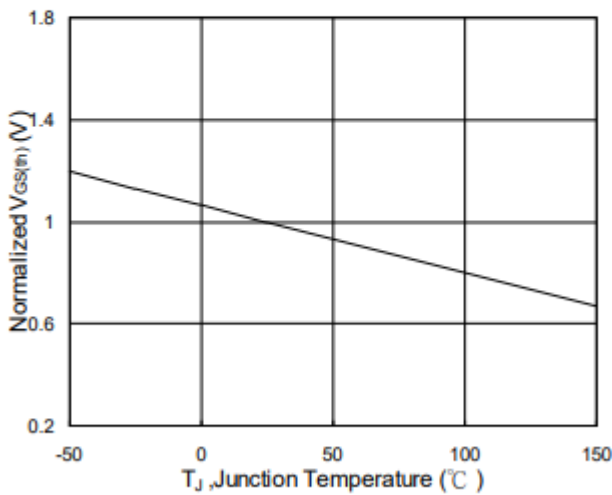


Fig.5 Normalized  $V_{GS(th)}$  vs.  $T_J$

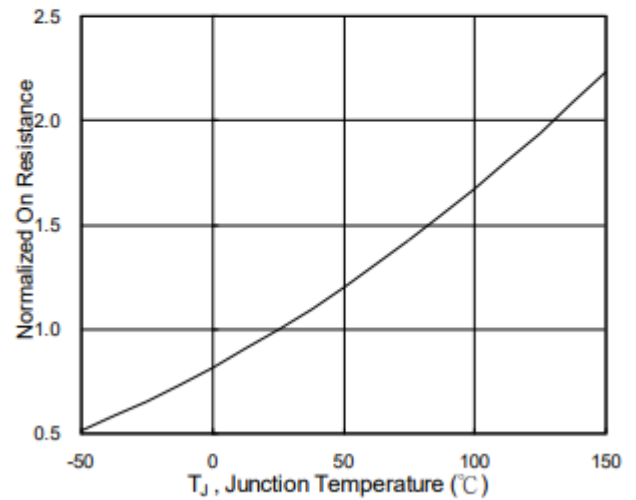


Fig.6 Normalized  $R_{DS(on)}$  vs.  $T_J$

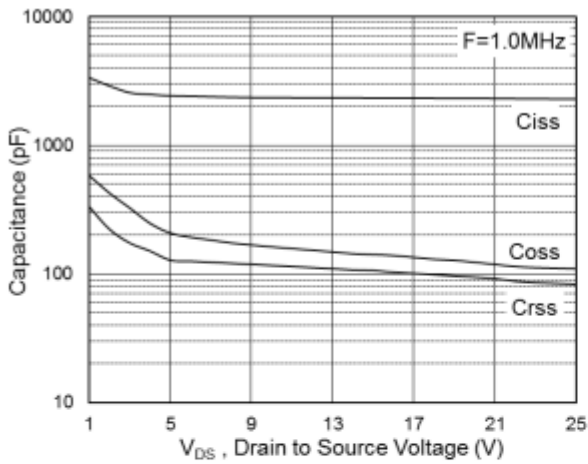


Fig.7 Capacitance

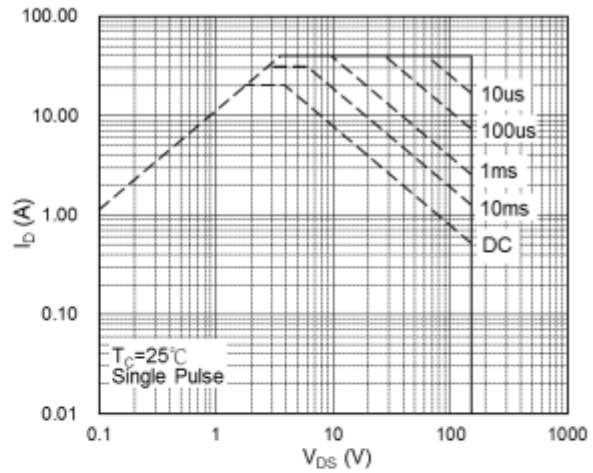


Fig.8 Safe Operating Area

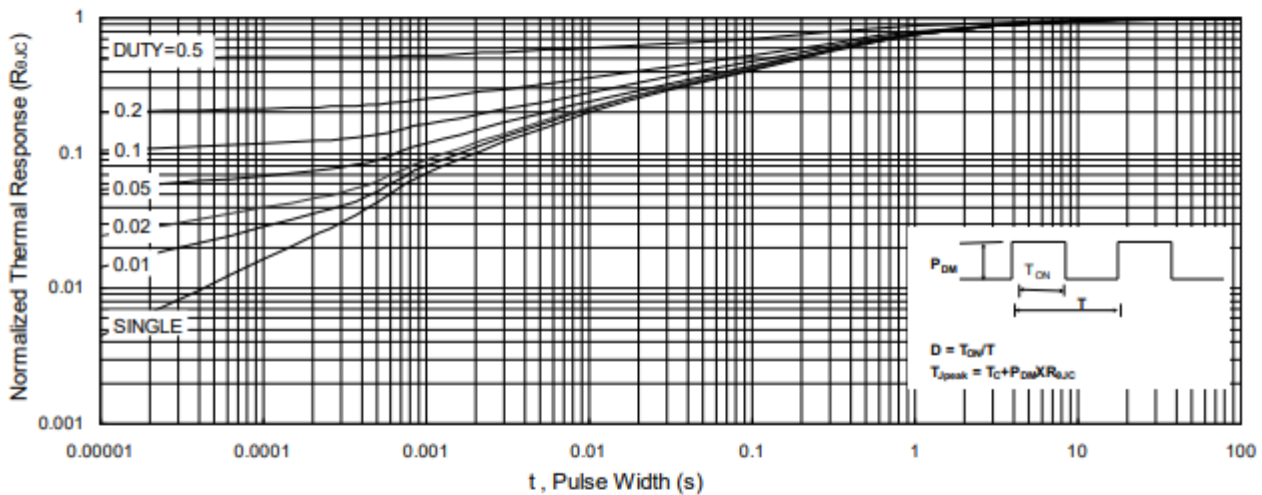


Fig.9 Normalized Maximum Transient Thermal Impedance

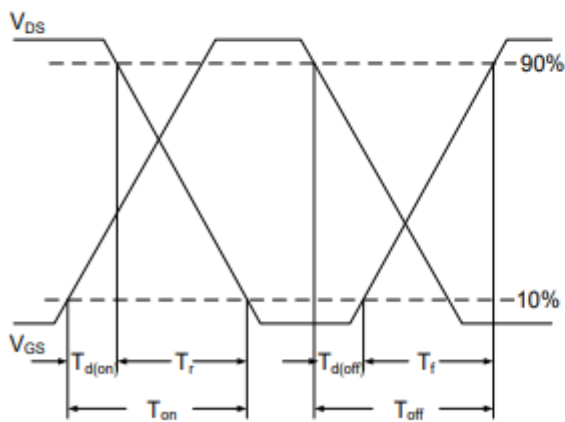


Fig.10 Switching Time Waveform

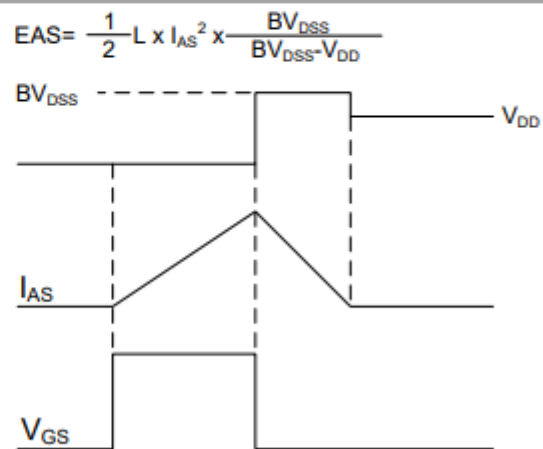
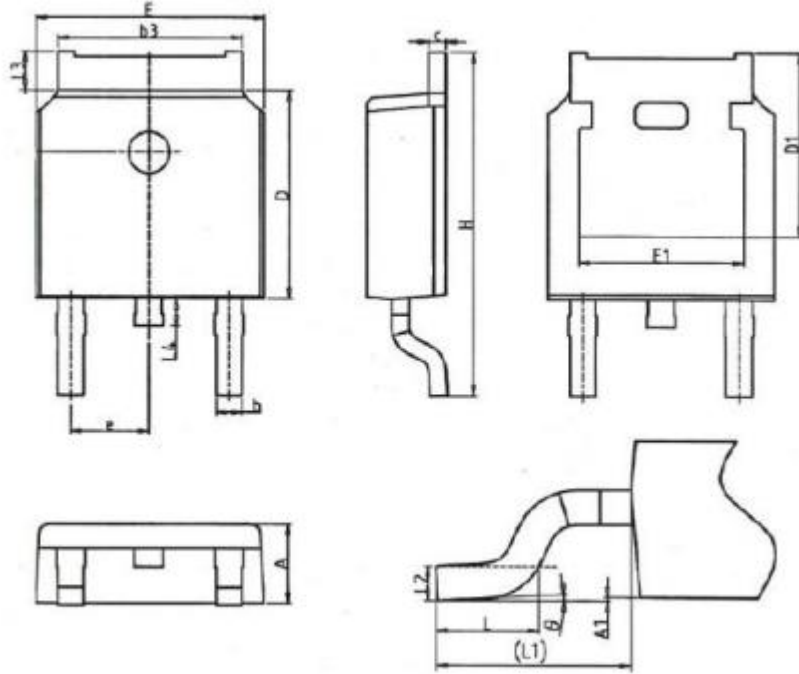


Fig.11 Unclamped Inductive Switching Waveform

### TO252-2L Package Outline



SYMBOLS	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	2.18	2.40	0.086	0.095
A1	-	0.2	-	0.008
b	0.68	0.9	0.026	0.036
b3	4.95	5.46	0.194	0.215
c	0.43	0.89	0.017	0.035
D	5.97	6.22	0.235	0.245
D1	5.300REF		0.209REF	
E	6.35	6.73	0.250	0.265
E1	4.32	--	0.170	-
e	2.286BSC		0.09BSC	
H	9.4	10.5	0.370	0.413
L	1.38	1.78	0.054	0.070
L1	2.90REF		0.114REF	
L2	0.51BSC		0.020BSC	
L3	0.88	1.28	0.034	0.050
L4	0.5	1	0.019	0.039
⊖	0°	8°	0°	8°